

# **RPT5032J**

The RPT5032J uses Rakon's new patented, Pluto+ ASIC. Pluto+ advances on the world famous, Pluto ASIC technology by providing enhanced frequency versus temperature stability. It also delivers to the industry the lowest jitter achievable from an ultra-stable TCXO. This allows the oscillator to comply with various standards including GR-1244, GR-253, G.812, G.813, G.8262 and G.827x.

#### **Features**

- Best in-class frequency versus temperature
- RMS phase jitter down to 0.13 ps
- Phase noise < -160 dBc/Hz floor
- Excellent holdover stability

## **Applications**

- Stratum 3 / IEEE 1588 / SyncE
- SONET / SDH / WDM / OTN
- Carrier Ethernet / Microwave
- Backhaul / Transport Equipment

### 5.0 x 3.2 x 1.75 mm

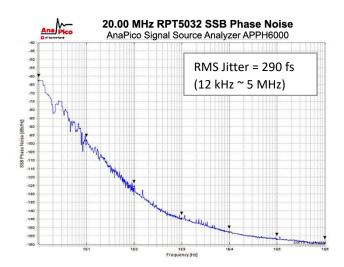


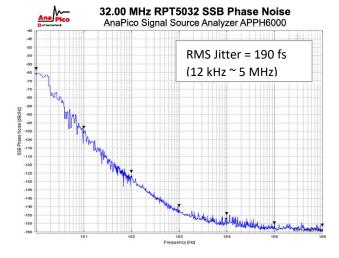
# **Standard Specifications**

Parameter	Min.	Тур.	Max.	Unit	Test Condition / Description
Nominal frequency (Fn)		10 – 40		MHz	Standard frequencies: 10, 12.8, 16.384, 19.44, 20, 20.48, 24.576, 25, 30.72, 38.88 and 40MHz
Operating temperature range	-40		85	°C	
Holdover stability, variable temperature			±100 - ±280	ppb	The default reference for holdover stability, variable temperature is (Fmax + Fmin)/2
Holdover stability, constant temperature			±10 - ±40	ppb	±10ppb after 10 days of continuous operation, ±40ppb after 48 hours of continuous operation
Slope over temperature ( $\Delta F/\Delta T$ )			±20 - ±100	ppb/°C	
Free-run accuracy			±4.6	ppm	Inclusive of calibration tolerance at 25°C, temperature, supply voltage variation ±5%, load variation ±5pF, reflow soldering and 20 years ageing reference to the nominal frequency
Wander generation					TDEV compliant with GR-1244 fig 5-4, G.812 types
TDEV / MTIE					II & III fig 2, G.813, G.8262  MTIE compliant with GR-1244 Fig 5-5, G.812 types II & III fig 1, G.813, G.8262
Supply voltage stability		±0.025		ppm	±5% variation, reference to frequency at nominal supply voltage
Acceleration stability		< 2		ppb/g	Gamma vector, 3-axes, 30-1500Hz
Start-up time			5 – 15	ms	90% amplitude
Root Allan Variance		5		10-11	tau = 1.0s
Supply voltage, V <sub>CC</sub>		3.3		V	±5%
Supply current	3		6	mA	Depending on nominal frequency
Oscillator output – HCMOS  Output voltage level high (V <sub>OH</sub> )  Output voltage level low (V <sub>OL</sub> )  Duty cycle  Rise & fall time  Load	0.9V <sub>cc</sub> 45	15	0.1V <sub>cc</sub> 55 8 30	V V % ns pF	LVCMOS & LVTTL compatible as per JESD8C  At 50% level Between 10% and 90%
Tri-state control Input level low (pin 6) Input level high (pin 6)	0.6V <sub>CC</sub>		0.2V <sub>CC</sub>	V V	Device disabled, output in high impedance state Device enabled, operating

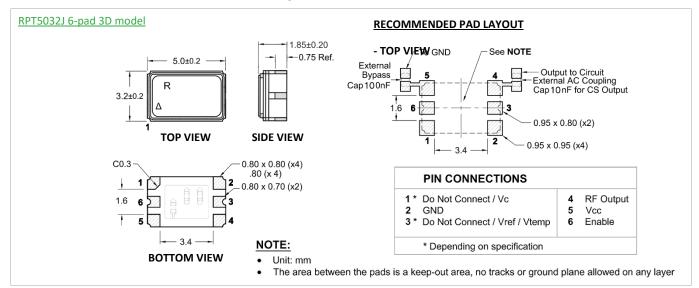


# SSB Phase Noise (Typical value at 25°C)





### **Model Outline and Recommended Pad Layout**



## **Test Circuit**

